TOSHIBA Bipolar Linear Integrated Circuit Silicon Monolithic

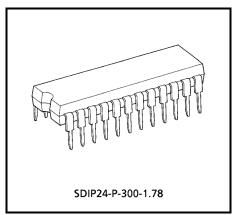
# TA2008ANG

# 5V AM / FM 1 Chip Tuner IC (for digital tuning system)

The TA2008ANG is the AM / FM 1 chip tuner IC, which is designed for radio cassette players and music centers. This is suitable for digital tuning system applications.

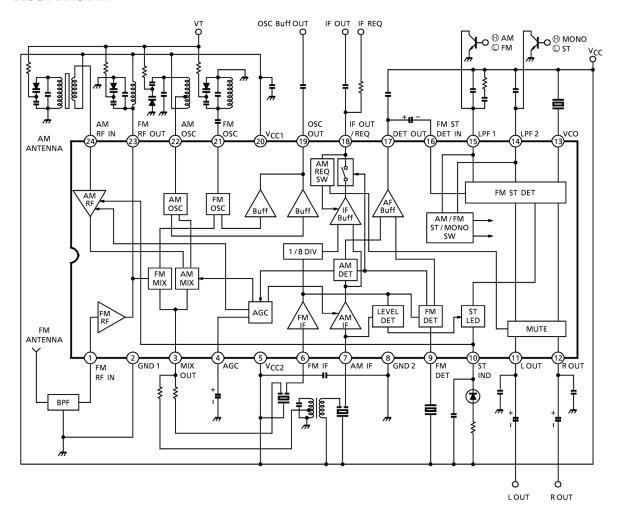
#### **Features**

- Suitable for combination with digital tuning system which is included IF counter.
- One terminal type AM / FM IF count output (auto stop signal) for IF counter of digital tuning system.
  - FM: 1.3375MHz (1 / 8 dividing)
  - AM: 450kHz
- Built-in mute circuit for IF count output.
- For adopting ceramic discriminator and ceramic resonator, it is not necessary to adjust the FM quad detector circuit and FM stereo detector vco circuit.
- Built-in one terminal type AM / FM local oscillator buffer output for digital tuning system applications.
- Operating supply voltage range: VCC = 3.5~14V (Ta = 25°C)



Weight: 1.2g (typ.)

#### **BLOCK DIAGRAM**



## **Explanation Of Terminals**

Pin	Characteristic	Internal Circuit	DC Voli (at no	tage (V) signal)
No.			AM	FM
1	FM-RF in	FM-RF OUT  23  1  CS  GND1 2	0	0.8
2	GND1 (GND for RF stage)	_	0	0
3	Mix out	VCC1 20 AM MIX FM MIX GND1 2 3	0.3	0.8
4	AGC	V <sub>CC2</sub> (5)	1.2	0.9
5	V <sub>CC2</sub> (V <sub>CC</sub> for IF / FM ST DET stage)	_	5.0	5.0
6	FM IF in	VCC2 (5) CD (8)	5.0	5.0

Pin	Characteristic	Characteristic Internal Circuit					
No.			AM	signal) É			
7	AM IF in	VCC2 (5 C) (7 (7 (7 (7 (7 (7 (7 (7 (7 (7 (7 (7 (7	5.0	5.0			
8	GND2 (GND for if / FM ST DET stage)	_	0	0			
9	QUAD (FM QUAD. Detector)	V <sub>CC2</sub> (5) (9) (1) (1) (1) (1) (1) (1) (1) (1) (1) (1	4.1	3.6			
10	St ind  • Stereo LED terminal  • Offset voltage cancel for AM RF amp.	19kHz  AM RF Amp	4.2	-			
11 12	L-out (L-ch output) R-out (R-ch output)	(1/12) GND2 (8)	1.35	1.35			

Pin	Characteristic	Internal Circuit	DC Voli (at no	tage (V) signal)
No.			AM	FM
13	VCO	VCC2 (5) (3) (3) (6) (6) (6) (6) (6) (6) (6) (6) (6) (6	5.0	4.1
14	LPF2  • LPF terminal for synchronous detector.  • VCO stop terminal  V <sub>14</sub> = GND → VCO stop	GND2 8	5.0	3.4
15	LPF1 • LPF terminal for phase detector • Bias terminal for AM / FM SW circuit $V_{15} = \text{GND} \rightarrow \text{AM}$ $V_{15} = \text{open} \rightarrow \text{FM}$	GND2 8	0	2.8
16	FM ST DET in	(16) MANUAL MANU	1.4	1.4

Pin No.	Characteristic	Internal Circuit	(at no	tage (V) signal)
INO.			AM	FM
17	DET out	VCC2 (5)  AM O FM 17)  B LOW→FM, HIGH→AM  B LOW→AM, HIGH→FM	1.4	1.4
18	IF out / REQ $V_{18} = \text{GND} \rightarrow \text{IF out}$	(E) (S) (S) (S) (S) (S) (S) (S) (S) (S) (S	4.0	4.0
19	OSC out	AM OSC 19 OSC GND1	4.0	4.0
20	V <sub>CC1</sub> (V <sub>CC</sub> for RF stage)	-	5.0	5.0
21	FM OSC	V <sub>CC1</sub> 20	5.0	5.0

Pin No.	Characteristic	Internal Circuit	DC Voltage (V) (at no signal)  AM FM		
INO.				FM	
22	AM OSC	② GND1	5.0	5.0	
23	FM RF out	cf. pin (1)	5.0	5.0	
24	AM RF in	VCC1 (2) AGC (24) GND2 (2)	5.0	5.0	

## Absolute Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit
Supply voltage	V <sub>CC</sub>	15	V
LED current	I <sub>LED</sub>	10	mA
LED voltage	V <sub>LED</sub>	15	V
Power dissipation	P <sub>D</sub> *	1200	mW
Operating temperature	T <sub>opr</sub>	-25~75	°C
Storage temperature	T <sub>stg</sub>	-55~150	°C

<sup>\* :</sup> Derated above Ta = 25°C in the proportion of 9.6mW / °C

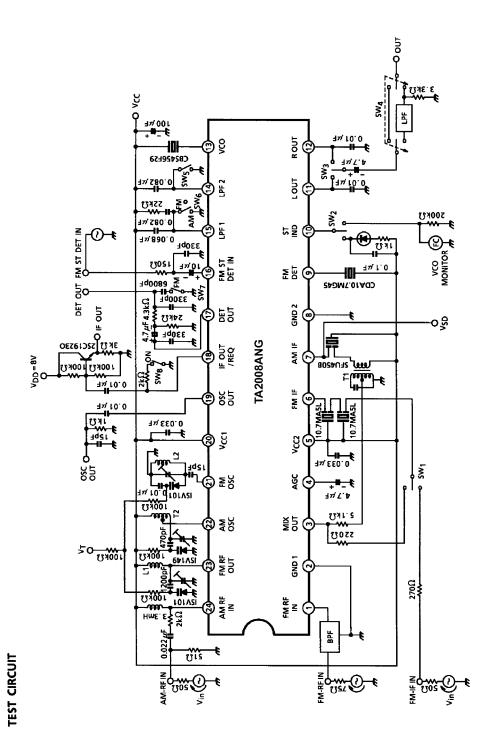
#### **Electrical Characteristics**

Unless Otherwise Specified, Ta = 25°C,  $V_{cc}$  = 5V, SW8: Off, F / E: f = 98MHz,  $f_m$  = 1kHz FM IF: f = 10.7MHz,  $\Delta f$  = ±22.5kHz,  $f_m$  = 1kHz  $\Delta M$ : f = 1MHz, MOD = 30%,  $f_m$  = 1kHz FM ST DET:  $f_m$  = 1kHz

Characteristic		Symbol	Test Cir– cuit	Test Condition	Min.	Тур.	Max.	Unit	
Sunn	ly current	I <sub>CC (FM)</sub>	I	V <sub>in</sub> = 0, FM mode	1	27	36	mA	
Оцрр	ny carrent	I <sub>CC (AM)</sub>	1	V <sub>in</sub> = 0. AM mode	-	18	25	IIIA	
./E	Input limiting voltage	V <sub>in</sub> (lim)		–3dB limiting with respect to V <sub>OD</sub> level at Vin = 60dBμV EMF		11		dBµV EMF	
ш	Local OSC buffer output voltage	V <sub>OSC</sub> (buff) FM	1	f <sub>OSC</sub> = 108.7MHz	90	180		mV <sub>rms</sub>	
	Input limiting voltage	V <sub>in</sub> (lim.) IF	ı	$-3$ dB limiting with respect to $V_{OD}$ level at $V_{in}$ = $80$ dB $\mu$ V EMF	40	45	50	dBµV EMF	
	Recovered output voltage V <sub>OD</sub> - V <sub>in</sub> = 80dBμV EMF		50	75	100	mV <sub>rms</sub>			
	Signal to noise ratio S / N — V <sub>in</sub> = 80dBµV EMF		1	70	1	dB			
<b>.</b> .	Total harmonic distortion THD - \		V <sub>in</sub> = 80dBμV EMF	I	0.3	ı	%		
FM IF	AM rejection ratio	M rejection ratio AMR — V <sub>in</sub> = 80dBμV EMF		V <sub>in</sub> = 80dBμV EMF	1	50		dB	
	SD output sensitivity $V_{SD}$ — $V_{SD} = V_{CC}-0.1V$		$V_{SD} = V_{CC} - 0.1V$	53	58	63	dBµV EMF		
	IF count output frequency	'   11/8   E (EM)     1V: = 800BUV EME \$\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\		1.3373	1.3375	1.3377	MHz		
	IF count output voltage	V1 / 8 IF (FM)	ı	V <sub>in</sub> = 80dBμV EMF,SW8: On	350	500	_	mV <sub>p-p</sub>	
	IF count output sensitivity	IF sens (FM)		SW8: On	49	54	59	dBµV EMF	

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Characteristic			Symbol	Test Cir– cuit	Test Condi	tion	Min.	Тур.	Max.	Unit
	Gain		G <sub>V</sub>	_	V <sub>in</sub> = 26dBµV EMF		20	45	80	$mV_{rms}$
	Recovered output voltage		V <sub>OD</sub>	_	V <sub>in</sub> = 60dBµV EMF		45	65	90	mV <sub>rms</sub>
	Signal to nois	se ratio	S/N	_	V <sub>in</sub> = 60dBµV EMF		_	42	_	dB
AM	Total harmor distortion	nic	THD	_	V <sub>in</sub> = 60dBµV EMF		_	1.0	_	%
	Local OSC b output voltag		V <sub>OSC</sub> (buff) AM	_	f <sub>OSC</sub> = 1.45MHz		90	150	_	mV <sub>rms</sub>
	IF count outp voltage	out	V <sub>IF</sub> (AM)	_	V <sub>in</sub> = 60dBµV EMF, S	SW8: On,	350	500	ı	mV <sub>p-p</sub>
	IF count outp sensitivity	out	IF sens (AM)	_	SW8: On		35	40	45	dBµV EMF
Din (1	Din (17) output registance		R17		FM mode		_	0.75	_	kΩ
	Pin (17) output resistance		IXII	_	AM mode		_	15.5	_	KX2
	Input resistar	nce	R <sub>IN</sub>	_			_	24	_	kΩ
	Output resistance		R <sub>OUT</sub>	_			_	5	_	kΩ
	Max. Composite signal input voltage		V <sub>in max</sub> (stereo)	_	L + R = 90%, P = 10%, SW4: LPF on f <sub>m</sub> = 1kHz, THD = 3%		_	800	_	mV <sub>rms</sub>
	Separation				P = 20mV <sub>ms</sub>	f <sub>m</sub> = 100Hz	1	42	-	dB
			Sep.	$ - P = 20 \text{mV}_{\text{rms}} $ $SW4: LPF \text{ on} $ $ f_{\text{m}} = 1 \text{kHz} $ $ f_{\text{m}} = 10 \text{kHz} $		f <sub>m</sub> = 1kHz	35	42	_	
					1	42	-	1		
⊨	Total harmonic	Monaural	THD (monaural)		V <sub>in</sub> = 200mV <sub>rms</sub>	V <sub>in</sub> = 200mV <sub>rms</sub>		0.1	_	%
FM St DET	distortion	Stereo	THD (stereo)	_	L + R = 180mV <sub>rms</sub> , P = 20mV <sub>rms</sub> , SW4: LPF on,		_	0.1	_	70
ᇤ	Voltage gain		G <sub>V</sub>	_	V <sub>in</sub> = 200mV <sub>rms</sub>		-2	0	2	dB
	Channel bala	ince	C. B.	_	V <sub>in</sub> = 200mV <sub>rms</sub>		-2	0	2	dB
	Stereo LED	On	V <sub>L (ON)</sub>		Pilot input			8	15	- mV <sub>rms</sub>
	sensitivity	Off	V <sub>L (OFF)</sub>	_	i not input		2	6	_	
	Stereo LED hysteresis		V <sub>H</sub>		To LED turn off from LED turn on		_	2	_	mV <sub>rms</sub>
	Capture rang	ie	C. R.	_	P = 15mV <sub>rms</sub>			±1.3		%
	Signal to nois	se ratio	S/N	_	V <sub>in</sub> = 200mV <sub>rms</sub>			80	_	dB
	Muting attenu	uation	MUTE	_	V <sub>in</sub> = 200mV <sub>rms</sub>			80		dB



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### **Coil Data**

Cail Na	Test	L	Co	0		Tu	rns		Wire	Deference
Coil No.	Freq.	(µH)	(pF)	$Q_0$	1–2	2–3	1–3	3–6	(mmφ)	Reference
L1 FM RF	100MHz			100				$2\frac{1}{2}$	0.5 UEW	Within core
L1 FM OSC	100MHz			100				$2\frac{1}{2}$	0.5 UEW	Within core
T1 AM mix	455kHz		180	48↑	47	111	158	4–6 20	0.06 UEW	(T): A7LCS-12064N
T2 AM OSC	796kHz	268		125	15	89			0.06 UEW	(S): 2157–2239–213A (T): A7BRS–11998Y

(S): Sumida electric co., Itd.

T2: AM OSC

(T): Toko co., Itd.

 $\begin{array}{c} \mathsf{L}_1 \ : \ \mathsf{FM} \ \mathsf{RF} \\ \mathsf{L}_2 \ : \ \mathsf{FM} \ \mathsf{OSC} \end{array}$ 

pin 3 C.F

T1: AM MIX

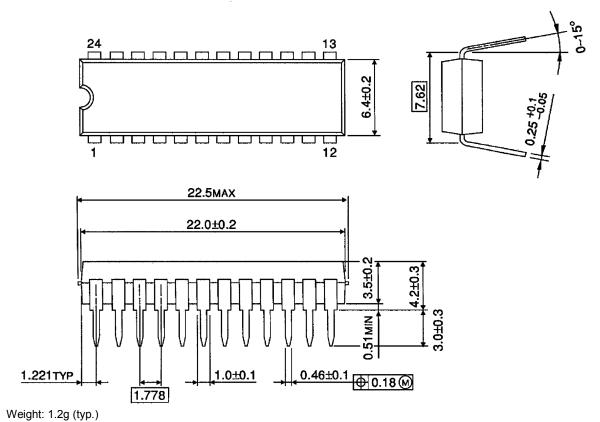
V.C pin@ VCC 1



## **Package Dimensions**

SDIP24-P-300-1.78

Unit: mm



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About solderability, following conditions were confirmed

- Solderability
  - (1) Use of Sn-37Pb solder Bath
    - · solder bath temperature = 230°C
    - · dipping time = 5 seconds
    - · the number of times = once
    - · use of R-type flux
  - (2) Use of Sn-3.0Ag-0.5Cu solder Bath
    - · solder bath temperature = 245°C
    - · dipping time = 5 seconds
    - · the number of times = once
    - · use of R-type flux